



ZXTN25060BZQ

60V NPN MEDIUM POWER TRANSISTOR IN SOT89

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

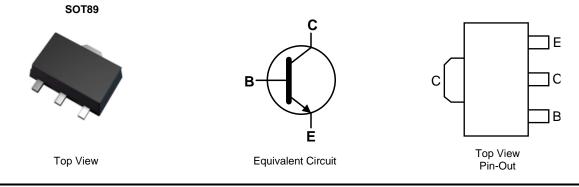
- BV_{CEX} > 150V
- BV_{CEO} > 60V
- BV_{ECO} > 6V
- I_C = 5A Continuous Collector Current
- V_{CE(sat)} < 70mV @ 1A
- $R_{CE(sat)} = 48m\Omega$ for a Low Equivalent On-Resistance
- Very Low Saturation Voltages
- Excellent hFE Characteristics
- 6V Reverse Blocking Capability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.055 grams (Approximate)

Applications

- Motor Driving (including DC fans)
- Solenoid, Relay and Actuator Drivers
- DC-DC Modules
- Power Switches
- MOSFET Gate Drivers



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25060BZQTA	Automotive	1C7	7	12mm	1,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

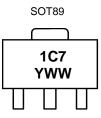
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1C7= Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 5 = 2015) WW = Week Code (01 ~ 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	150	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	lc	5	A
Base Current	IB	1	A
Peak Pulse Current	I _{CM}	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		1.1		
Power Dissinction	(Note 7)		1.8	W	
Power Dissipation	(Note 8)	P _D	2.4		
	(Note 9)	-	4.46		
	(Note 6)		117		
Thermal Desistance Innetion to Ambient Air	(Note 7)		68		
Thermal Resistance, Junction to Ambient Air	(Note 8)	R _{θJA}	51	°C/W	
	(Note 9)	-	28		
Thermal Resistance, Junction to Lead	(Note 10)	R _{θJL}	8]	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

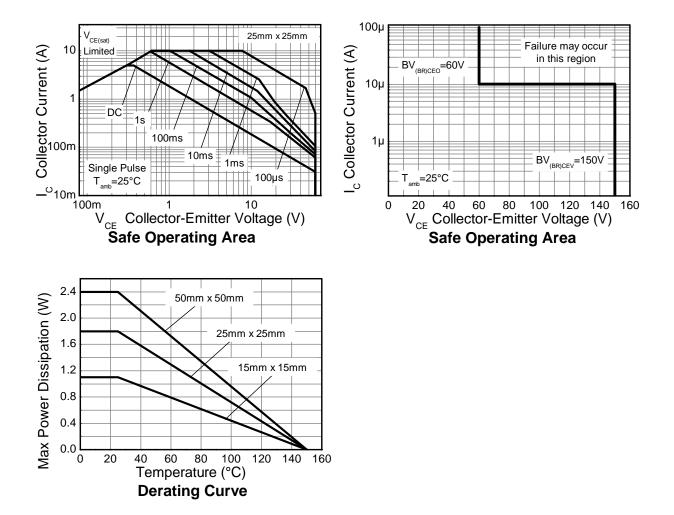
8. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.

9. Same as Note 7 measured at t<5 seconds.

Thermal resistance from junction to solder-point (on the exposed collector pad).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.

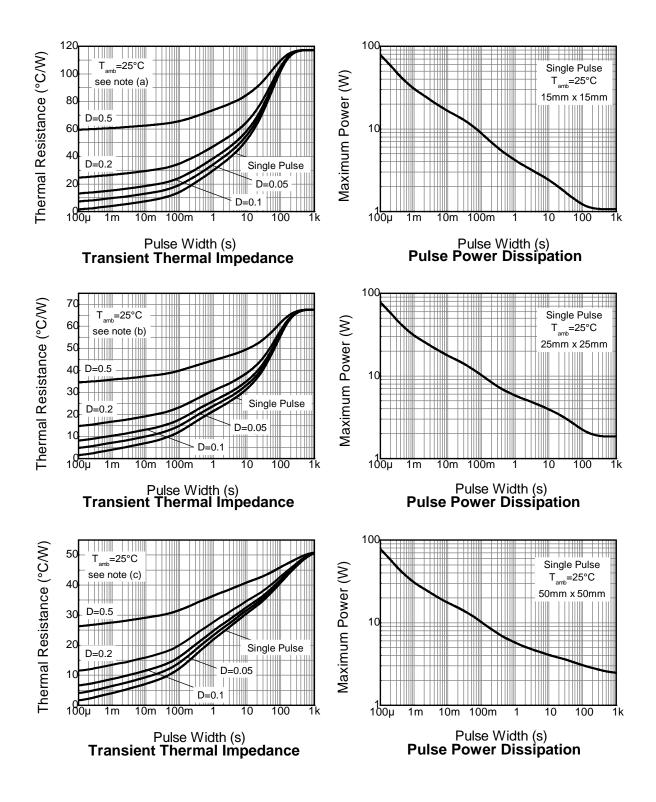


Thermal Characteristics and Derating Information





Thermal Characteristics and Derating Information (continued)





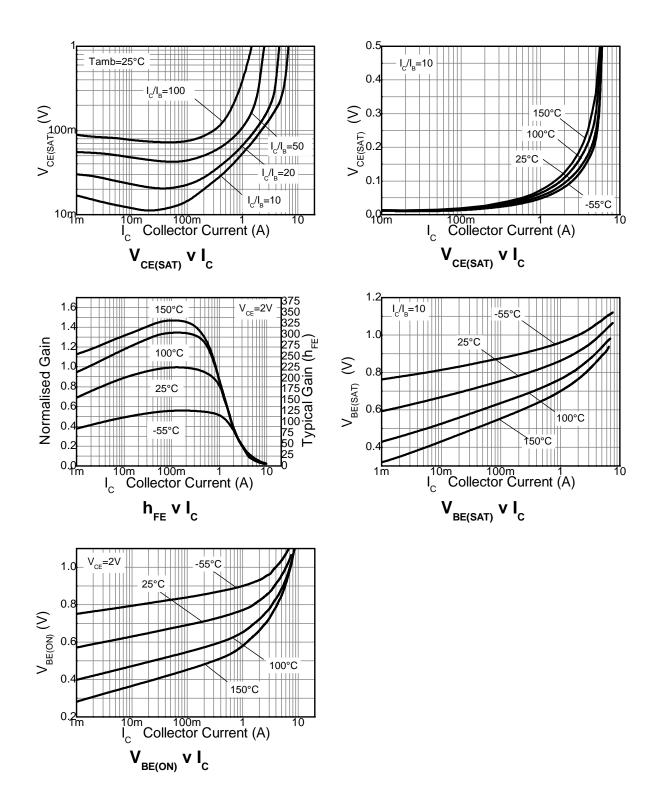
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Forward Blocking)	BV _{CEX}	150	190	—	V	$I_C = 100 \mu A, \ R_{BE} \leq 1 k \Omega \ \text{or} \\ -1 V < V_{BE} < 0.25 V$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	60	80	—	V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.0	—	V	$I_E = 100 \mu A$
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	6	8	—	V	$I_{E} = 100 \mu A, R_{BC} \le 1 k \Omega \text{ or} \\ <0.25 V > V_{BC} > 0.25 V$
Emitter-Collector Breakdown Voltage (Base Open)	BV _{ECO}	6	7	—	V	I _E = 100μA
Collector-Base Cutoff Current	Ісво	—	<1	50 20	nA μA	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector-Emitter Cutoff Current	ICEX	—	_	100	nA	V_{CE} = 120V, $R_{BE} \le 1k\Omega$ or -1V < $V_{BE} < 0.25V$
Emitter-Base Cutoff Current	I _{EBO}	_	<1	50	nA	V _{EB} = 5.6V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	_	55 70 185 240	70 90 230 305	mV	$\label{eq:lc} \begin{array}{l} I_{C} = 1A, \ I_{B} = 100 mA \\ I_{C} = 1A, \ I_{B} = 50 mA \\ I_{C} = 4A, \ I_{B} = 400 mA \\ I_{C} = 5A, \ I_{B} = 500 mA \end{array}$
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	—	1,020	1,100	mV	$I_{C} = 5A, I_{B} = 500mA$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(on)}	_	960	1,050	mV	$I_C = 5A, V_{CE} = 2V$
DC Current Gain (Note 12)	hfe	100 90 45 —	200 180 90 20	300 — — —	_	$\label{eq:linear} \begin{array}{l} I_{C} = 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} = 1 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} = 2 \text{A}, \ V_{CE} = 5 \text{OV} \\ I_{C} = 5 \text{A}, \ V_{CE} = 5 \text{V} \end{array}$
Transitional Frequency	f⊤	_	185	_	MHz	I _C = 100mA, V _{CE} = 5V f=100MHz
Output Capacitance	Cobo	—	11.5	20	pF	V _{CB} = 10V, f=1MHz
Delay Time	t _d	_	16	_	ns	
Rise Time	tr	_	15	—	ns	$V_{CC} = 10V,$
Storage Time	ts	_	509	—	ns	$I_{CC} = 500 \text{mA}$ $I_{B1} = -I_{B2} = 50 \text{mA}$
Fall Time	t _f		57	_	ns	

Note: 12. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



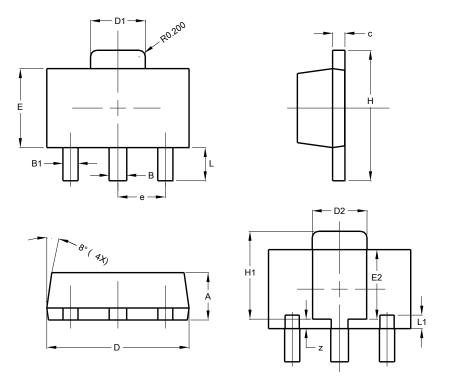
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

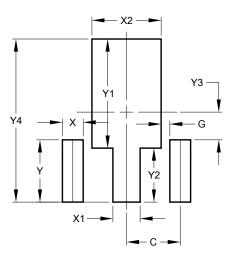
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT89					
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
z	0.20	0.40	0.30			
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		



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